

PBSS4360Z

60 V, 3 A NPN low VCEsat (BISS) transistor

26 February 2014

Product data sheet

1. General description

NPN low V_{CEsat} Breakthrough In Small Signal (BISS) transistor in a medium power SOT223 (SC-73) Surface-Mounted Device (SMD) plastic package.

PNP complement: PBSS5360Z.

2. Features and benefits

- Low collector-emitter saturation voltage V_{CEsat}
- High collector current capability I_C and I_{CM}
- High energy efficiency due to less heat generation
- AEC-Q101 qualified

3. Applications

- DC-to-DC conversion
- Supply line switching
- Battery charger
- LCD backlighting
- Driver in low supply voltage applications (e.g. lamps and LEDs)
- Inductive load driver (e.g. relays, buzzers and motors)

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{CEO}	collector-emitter voltage	open base	-	-	60	V
I _C	collector current		-	-	3	Α
I _{CM}	peak collector current	$t_p \le 1$ ms; single pulse	-	-	6	Α
R _{CEsat}	collector-emitter saturation resistance	I_{C} = 2 A; I_{B} = 200 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02; \ T_{amb}$ = 25 °C	-	-	140	mΩ



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base	4	2, 4
2	С	collector		1—
3	Е	emitter		. 1
4	С	collector	☐1 ☐2 ☐3 SC-73 (SOT223)	3 sym016

6. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
PBSS4360Z	SC-73	plastic surface-mounted package with increased heatsink; 4 leads	SOT223		

7. Marking

Table 4. Marking codes

Type number	Marking code
PBSS4360Z	P4360Z

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{CBO}	collector-base voltage	open emitter		-	80	V
V _{CEO}	collector-emitter voltage	open base		-	60	V
V _{EBO}	emitter-base voltage	open collector		-	7	V
I _C	collector current			-	3	Α
I _{CM}	peak collector current	$t_p \le 1$ ms; single pulse		-	6	Α
I _B	base current			-	500	mA
I _{BM}	peak base current	$t_p \le 1$ ms; single pulse		-	1	Α
P _{tot}	total power dissipation		[1]	-	0.65	W
			<u>[2]</u>	-	1	W
			<u>[3]</u>	-	1.35	W

PBSS4360Z

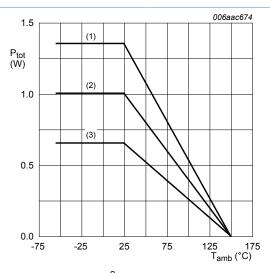
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Symbol	Parameter	Conditions		Min	Max	Unit
			<u>[4]</u>	-	2	W
T _j	junction temperature			-	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².
- [4] Device mounted on an FR4 PCB, 70 μm single-sided copper, tin-plated, mounting pad for collector 6 cm².



- (1) FR4 PCB, mounting pad for collector 6 cm²
- (2) FR4 PCB, mounting pad for collector 1 cm²
- (3) FR4 PCB, standard footprint

Fig. 1. Power derating curves

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9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
ang a)	thermal resistance		[1]	-	-	192	K/W
	from junction to		[2]	-	-	125	K/W
	ambient		[3]	-	-	93	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	-	16	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².

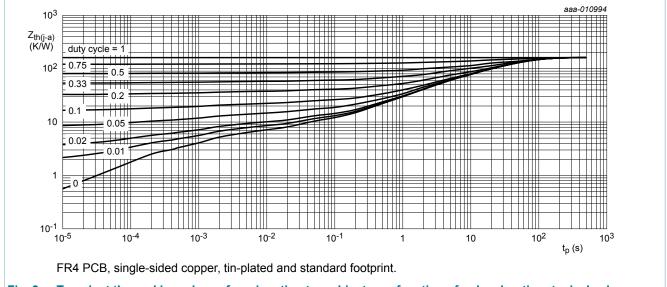
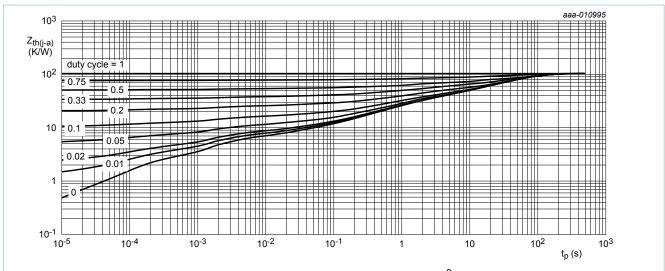


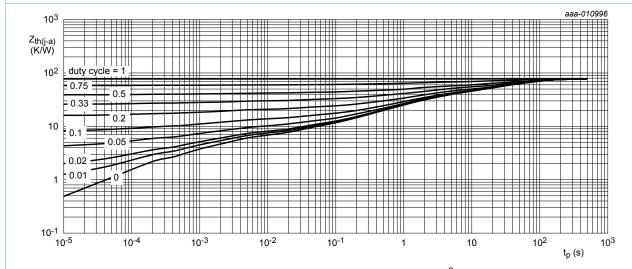
Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².

Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².

Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

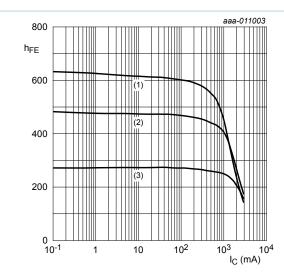
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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{CBO}	collector-base cut-off	V_{CB} = 48 V; I_{E} = 0 A; T_{amb} = 25 °C	-	-	100	nA
	current	V_{CB} = 48 V; I_{E} = 0 A; T_{j} = 150 °C	-	-	50	μA
I _{CES}	collector-emitter cut-off current	V _{CE} = 48 V; V _{BE} = 0 V; T _{amb} = 25 °C	-	-	100	nA
l _{ЕВО}	emitter-base cut-off current	$V_{EB} = 5 \text{ V}; I_{C} = 0 \text{ A}; T_{amb} = 25 \text{ °C}$	-	-	100	nA
h _{FE}	DC current gain	V_{CE} = 5 V; I_{C} = 50 mA; T_{amb} = 25 °C	200	-	-	
		V_{CE} = 5 V; I_{C} = 500 mA; pulsed; $t_{p} \le$ 300 µs; $\delta \le$ 0.02; T_{amb} = 25 °C	200	-	-	
		V_{CE} = 5 V; I_{C} = 1 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	200	-	-	
		V_{CE} = 5 V; I_{C} = 2 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	120	-	-	
		V_{CE} = 5 V; I_{C} = 3 A; pulsed; t_{p} ≤ 300 μ s; δ ≤ 0.02; T_{amb} = 25 °C	75	-	-	
OLSat	collector-emitter saturation voltage	I_{C} = 500 mA; I_{B} = 50 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02; \ T_{amb}$ = 25 °C	-	-	75	mV
		I_C = 1 A; I_B = 100 mA; pulsed; $t_p \le 300$ μs; δ ≤ 0.02; T_{amb} = 25 °C	-	-	150	mV
		I_{C} = 2 A; I_{B} = 200 mA; pulsed; $t_{p} \le 300 \ \mu s$; $\delta \le 0.02$; T_{amb} = 25 °C	-	-	275	mV
		I_C = 3 A; I_B = 300 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	-	400	mV
R _{CEsat}	collector-emitter saturation resistance	I_C = 2 A; I_B = 200 mA; pulsed; $t_p \le 300$ μs; $\delta \le 0.02$; T_{amb} = 25 °C	-	-	140	mΩ
V _{BEsat}	base-emitter saturation voltage	I_{C} = 1 A; I_{B} = 100 mA; pulsed; $t_{p} \le 300 \ \mu s$; $\delta \le 0.02$; T_{amb} = 25 °C	-	-	1.2	V
V_{BEon}	base-emitter turn-on voltage	V_{CE} = 5 V; I_{C} = 1 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	-	1.1	V
fτ	transition frequency	V_{CE} = 10 V; I_{C} = 50 mA; f = 100 MHz; T_{amb} = 25 °C	75	145	-	MHz
C _c	collector capacitance	V_{CB} = 10 V; I_{E} = 0 A; i_{e} = 0 A; f = 1 MHz; T_{amb} = 25 °C	-	11	14	pF

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$$V_{CE} = 5 V$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = -55$$
 °C

Fig. 5. DC current gain as a function of collector current; typical values

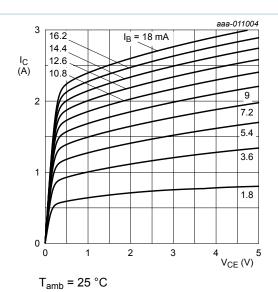
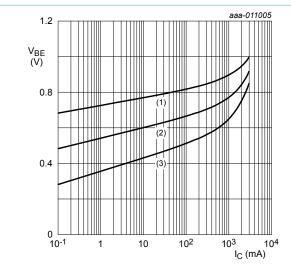


Fig. 6. Collector current as a function of collectoremitter voltage; typical values



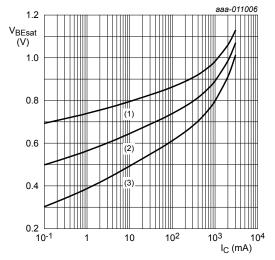
$$V_{CE} = 5 V$$

(1)
$$T_{amb} = -55 \, ^{\circ}C$$

(2)
$$T_{amb}$$
 = 25 °C

(3)
$$T_{amb} = 100 \, ^{\circ}C$$

Fig. 7. Base-emitter voltage as a function of collector current; typical values



$$I_{\rm C}/I_{\rm B} = 20$$

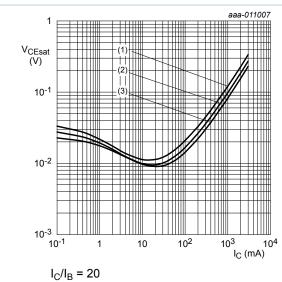
(1)
$$T_{amb} = -55 \, ^{\circ}C$$

(2)
$$T_{amb}$$
 = 25 °C

(3)
$$T_{amb} = 100 \, ^{\circ}C$$

Fig. 8. Base-emitter saturation voltage as a function of collector current; typical values

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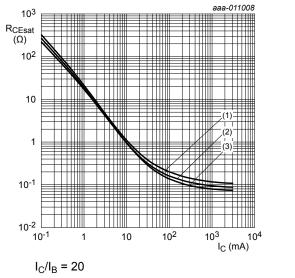
$$I_{\rm C}/I_{\rm B} = 20$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb}$$
 = 25 °C

(3)
$$T_{amb} = -55 \, ^{\circ}C$$

Fig. 9. Collector-emitter saturation voltage as a function of collector current; typical values



(1)
$$T_{amb}$$
 = 100 °C

(2)
$$T_{amb}$$
 = 25 °C

(3)
$$T_{amb} = -55 \, ^{\circ}C$$

Fig. 10. Collector-emitter saturation resistance as a function of collector current; typical values

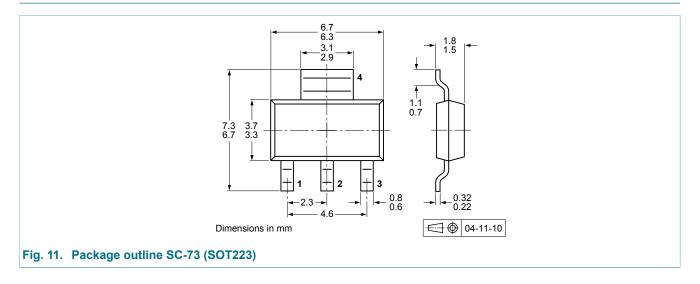
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11. Test information

11.1 Quality information

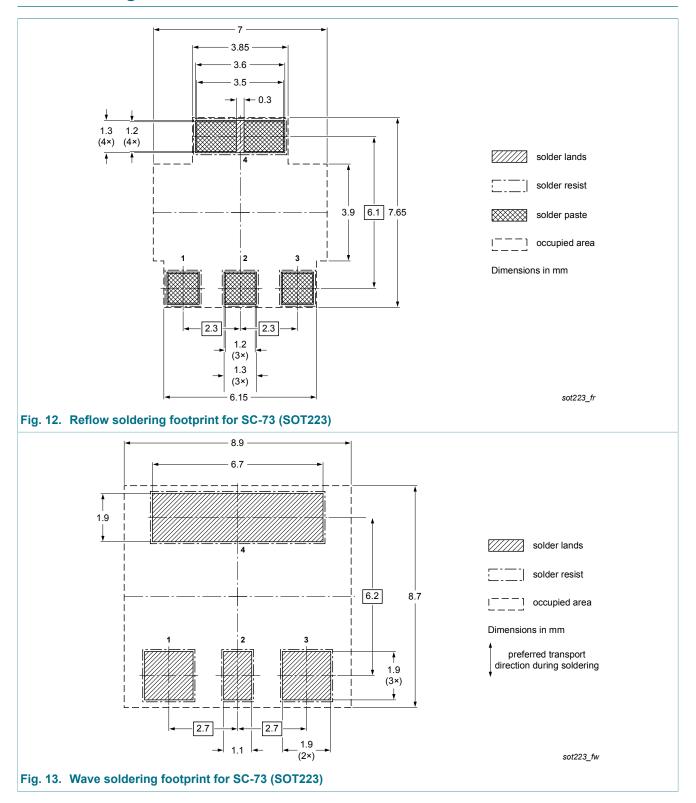
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

12. Package outline



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13. Soldering



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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PBSS4360Z v.1	20140226	Product data sheet	-	-

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